Homework Assignment 6 (Due Mar. 4th at the beginning of the class)

(1) **[Transistor Sizing, 5 points]** $\mu_n = 2\mu_p$. *R* is the resistance of a 1X NMOS transistors. The target time constant is *RC* where *C* is the load capacitance. Size the transistors in the following figure to satisfy the target time constant (try not to over-optimize them).



Each path goes through four TRs, so the size of each NMOS is 4X and the size of each PMOS is 8X.

(2) [Transistor Sizing, 5 points] *R* is the resistance of a 1X NMOS transistor. The target time constant is *RC* where *C* is the load capacitance. Size the transistors in the following pull-down network to satisfy the time constant. However, <u>minimize</u> the total width of the transistors.



A and C are connected in parallel, so let's upsize them to aX. B, D, and E are connected in parallel, so let's upsize them to bX. Then the total width is W = 2a + 3b. Constraint: $\frac{R}{a} + \frac{R}{b} = R \implies b = \frac{a}{a-1} \implies W = 2a + \frac{3a}{a-1} \implies W' = 2 + \frac{3(a-1)-3a}{(a-1)^2} = \frac{2(a-1)^2-3}{(a-1)^2} =$

 $2a^2 - 4a - 1 = 0 \implies a = 1 + \frac{\sqrt{6}}{2}, b = \frac{\sqrt{6}}{3}$

0

(3) **[Elmore Delay, 5 points]** Compute Elmore delay at Sink 1 and Sink 2 in the following figure.





19.5ps + 22ps + 440ps = 551.5ps

(4) [Switching Characteristics, 5 points] Compute the rise time at the output node in the following figure. C₁ and C₂ are parasitic capacitances at the internal nodes. The input switches from (A, B, C, D, E, F) = (1, 0, 0, 0, 0, 0) to (0, 0, 0, 1, 0, 1). Use R_X (where X=A, B, C, D, E, F) for the resistance of transistor X.



When (A, B, C, D, E, F)=(1, 0, 0, 0, 0, 0), C_1 and C_2 (and C_L) are fully discharged. When (A, B, C, D, E, F) switch to (0, 0, 0, 1, 0, 1), only A, B, C, and E are turned on. Thus,

$$\tau = R_E \cdot C_L + \frac{R_B \cdot R_C}{R_B + R_C} \cdot (C_2 + C_L) + R_A \cdot (C_1 + C_2 + C_L)$$

delay= 2.2τ